

The documentation and process conversion measures necessary to comply with this revision shall be completed by 14 June 2016.

INCH-POUND
MIL-PRF-19500/765B
14 March 2016
SUPERSEDING
MIL-PRF-19500/765A
18 March 2013

PERFORMANCE SPECIFICATION SHEET

- * SEMICONDUCTOR DEVICE, DIODE, SILICON, DUAL SCHOTTKY, COMMON CATHODE, ENCAPSULATED (THROUGH-HOLE AND SURFACE MOUNT), TYPE 1N7072, AND 1N7078 JAN, JANTX, JANTXV, AND JANS

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of this specification sheet and [MIL-PRF-19500](#).

1. SCOPE

- * 1.1 Scope. This specification covers the performance requirements for a silicon, dual Schottky, center-tap power rectifier diode for use in high frequency switching power supplies and resonant power converters. Four levels of product assurance (JAN, JANTX, JANTXV, and JANS) are provided for each encapsulated device.
- * 1.2 Package outlines. The device package outlines are as follows: U3 in accordance with [figure 1](#) and T3 (TO-257AA) in accordance with [figure 2](#) for all encapsulated device types.

1.3 Maximum ratings. Unless otherwise specified, $T_A = +25^\circ\text{C}$.

Column 1	Column 2	Column 3	Column 4	Column 5		Column 6
Types	V_{RWM}	I_O (1) (2)	I_{FSM} (3) $t_p = 8.3 \text{ ms}$ $T_C = +25^\circ\text{C}$	$R_{\theta JC}$ (2) (4)	$R_{\theta JC}$ (3) (4)	T_{STG} and T_J
	V dc	A dc	A (pk)	$^\circ\text{C/W}$	$^\circ\text{C/W}$	$^\circ\text{C}$
1N7072CCT3	30	16A	150A	0.8	1.6	-65 to +150
1N7078U3	30	30A	150A	1.6	1.6	-65 to +150

- (1) See temperature-current derating curves on figures [3](#) and [4](#).
(2) Entire package.
(3) Each leg.
(4) See thermal impedance curves on figures [5](#) and [6](#).

1.4 Primary electrical characteristics. $R_{\theta JC} = 0.8^\circ\text{C/W}$ maximum entire package for 1N7072CCT3; $R_{\theta JC} = 1.6^\circ\text{C/W}$ maximum entire package for 1N7078U3.

Comments, suggestions, or questions on this document should be addressed to DLA Land and Maritime, ATTN: VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to Semiconductor@dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.dla.mil/>.

AMSC N/A

FSC 5961



- * 1.5 Part or Identifying Number (PIN). The PIN is in accordance with [MIL-PRF-19500](#), and as specified herein. See [6.5](#) for PIN construction example and [6.6](#) for a list of available PINs.
- * 1.5.1 JAN certification mark and quality level for encapsulated devices. The quality level designators for encapsulated devices that are applicable for this specification sheet from the lowest to the highest level are as follows: "JAN", "JANTX", "JANTXV" and "JANS".
- * 1.5.2 Device type. The designation system for the device types of diodes covered by this specification sheet are as follows.
 - * 1.5.2.1 First number and first letter symbols. The diodes of this specification sheet are identified by the first number and letter symbols "1N".
 - * 1.5.2.2 Second number symbols. The second number symbols for the diodes covered by this specification sheet are as follows: "7072CC" and "7078".
 - * 1.5.2.3 Suffix letters. The suffix letters "U3" are used on devices that are packaged in the surface mount package of [figure 1](#). The suffix letters "T3" are used on devices that are packaged in the TO-257AA through hole package of [figure 2](#).
- * 1.5.3 Lead finish. The lead finishes applicable to this specification sheet are listed on [QPDSIS-19500](#).

2. APPLICABLE DOCUMENTS

- * 2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

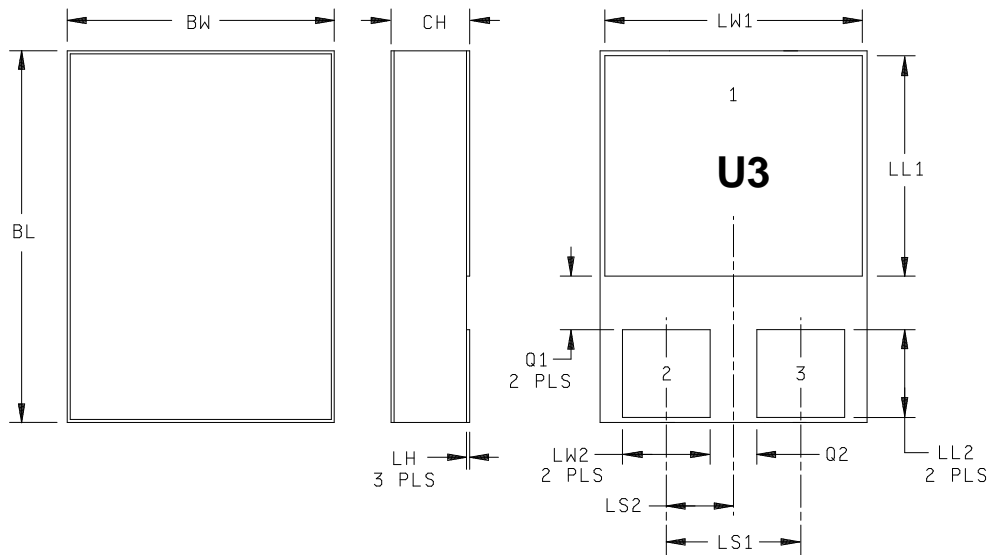
[MIL-PRF-19500](#) - Semiconductor Devices, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

[MIL-STD-750](#) - Test Methods for Semiconductor Devices.

- * (Copies of these documents are available online at <http://quicksearch.dla.mil/>).

2.3 Order of precedence. Unless otherwise noted herein or in the contract, in the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.



1N7078U3

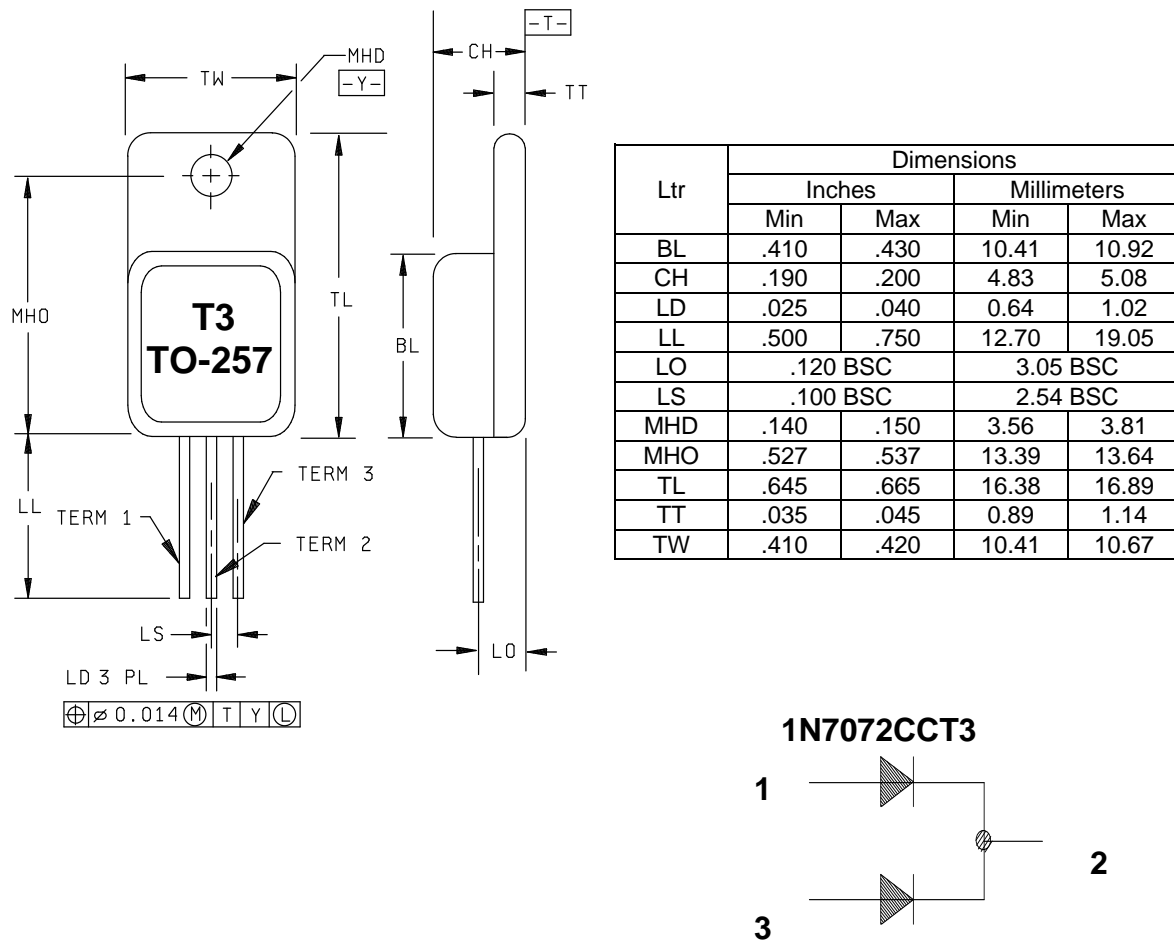
1 ———  **2, 3**

Ltr	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.395	.405	10.03	10.29
BW	.291	.301	7.39	7.65
CH	.108	.122	2.74	3.12
LH	.010	.020	0.25	0.51
LL1	.220	.230	5.59	5.84
LL2	.115	.125	2.92	3.18
LS1	.150 BSC		3.81 BSC	
LS2	.075 BSC		1.91 BSC	
LW1	.281	.291	7.14	7.39
LW2	.090	.100	2.29	2.54
Q1	.030		0.76	
Q2	.030		0.76	

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Dimensions are in accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.
4. Suffix "U3C" indicates a ceramic lid on package.

FIGURE 1. Dimensions and configuration, 1N7078U3.



NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

FIGURE 2. Dimensions and configuration for 1N7072CCT3 (TO-257AA).

3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in [MIL-PRF-19500](#) and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see [4.2](#) and [6.3](#)).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in [MIL-PRF-19500](#).

3.4 Interface and physical dimensions. The interface and physical dimensions shall be as specified in [MIL-PRF-19500](#), and on figures [1](#) and [2](#) herein. Methods used for electrical isolation of the terminal feedthroughs for the TO-257 package shall employ materials that contain a minimum of 90 percent Al_2O_3 (ceramic).

3.4.1 Polarity. Polarity and terminal configuration shall be in accordance with figures [1](#) and [2](#) herein.

3.4.2 Lead material, finish, and formation. Lead material for the TO-257 package shall be Kovar, Alloy 52, or CuZr; a copper core or plated core is permitted. Lead finish shall be solderable in accordance with [MIL-PRF-19500](#), [MIL-STD-750](#), and herein. Where a choice of lead formation, material, or finish is desired, it shall be specified in the acquisition document (see [6.2](#)). When lead formation is performed, as a minimum, the vendor shall perform 100 percent hermetic seal in accordance with screen 14 of table E-IV of [MIL-PRF-19500](#) and 100 percent dc testing in accordance with [table I](#), subgroup 2 herein.

3.5 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in [1.3](#), [1.4](#), and [table I](#) herein.

3.6 Electrical test requirements. The electrical test requirements shall be as specified in tables I and II herein.

3.7 Marking. Marking shall be in accordance with [MIL-PRF-19500](#) and herein.

3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see [4.2](#)).
- b. Screening (see [4.3](#)).
- c. Conformance inspection (see [4.4](#) and [tables I and II](#) herein).

4.2 Qualification inspection. Qualification inspection shall be in accordance with [MIL-PRF-19500](#) and as specified herein.

4.2.1 Group E qualification. Group E inspection shall be performed for qualification or re-qualification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of [table III](#) tests, the tests specified in [table III](#) herein that were not performed in the prior revision shall be performed on the first inspection lot of this revision to maintain qualification.

4.3 Screening (JANS, JANTXV, and JANTX levels). Screening shall be in accordance with table E-IV of MIL-PRF-19500 and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (table E-IV of MIL-PRF-19500)	Measurement	
	JANS level	JANTX and JANTXV levels
3b	Method 4066 of MIL-STD-750, condition A, one pulse, $t_p = 8.3$ ms, $I_O = 0$, $V_{RWM} = 0$, $I_{FSM} =$ see 1.3 herein.	Method 4066 of MIL-STD-750, condition A, one pulse, $t_p = 8.3$ ms, $I_O = 0$, $V_{RWM} = 0$, $I_{FSM} =$ see 1.3 herein.
3c	Thermal impedance (see 4.3.2).	Thermal impedance (see 4.3.2).
3d	Avalanche energy test (see 4.3.3).	Avalanche energy test (see 4.3.3).
9, 10	Not applicable.	Not applicable.
11	V_{F1} and I_{R1} .	V_{F1} and I_{R1} .
12	See 4.3.1. 240 hours, minimum.	See 4.3.1. 48 hours minimum.
13	Subgroups 2 and 3 of table I herein, V_{F1} , V_{F2} , V_{F3} , and I_{R1} ; $\Delta V_{F1} = \pm 50$ mV (pk); $\Delta V_{F2} = \pm 50$ mV (pk); $\Delta V_{F3} = \pm 50$ mV (pk); $\Delta I_{R1} = \pm 100$ percent from the initial value or ± 500 uA, whichever is greater.	Subgroup 2 of table I herein; V_{F1} , V_{F2} , V_{F3} , and I_{R1} ; $\Delta V_{F1} = \pm 50$ mV (pk); $\Delta V_{F2} = \pm 50$ mV (pk); $\Delta V_{F3} = \pm 50$ mV (pk); $\Delta I_{R1} = \pm 100$ percent from the initial value or ± 500 uA, whichever is greater.

4.3.1 High temperature reverse bias. Reverse bias conditions are as follows: Method 1038 of MIL-STD-750, test condition A, $V_R = 24$ V dc; $T_J = +100^\circ\text{C}$.

* 4.3.2 Thermal impedance. The thermal impedance measurements shall be performed in accordance with method 3101 or 4081 of MIL-STD-750 using the guidelines in that method for determining I_M , I_H , t_H , and t_{MD} . See table III, subgroup 4 and figures 5 and 6 herein.

4.3.3 Avalanche energy test. The avalanche energy test is to be performed in accordance with method 4064 of MIL-STD-750 using the circuit as shown on figure 7 or equivalent. The Schottky rectifier under test must be capable of absorbing the reverse energy, as follows: $I_{AS} = 1$ A, $V_{br} = 30$ V minimum, $L = 100$ μH .

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with table E-V of MIL-PRF-19500, and table I herein. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table II herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in tables E-VIA (JANS) and E-VIB (JAN, JANTX, and JANTXV) of MIL-PRF-19500 and as follows. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2, forward voltage test (V_{F1}) and reverse leakage test (I_{R1}) herein. Delta measurements shall be in accordance with table II herein.

* 4.4.2.1 Quality level JANS, table E-VIA of MIL-PRF-19500.

	Subgroup	Method	Condition
*	B4	1037	$\Delta T_C = +85^\circ\text{C}$, $I_F = 2$ A minimum.
	B5	1038	Condition A, $V_R = 24$ V dc, $T_J = +100^\circ\text{C}$, $t = 340$ hours min; heat sinking allowed. This test shall be extended to 1,000 hours for each wafer.
			As an alternative method a ten dice sample (or 1 die per wafer whichever is greater) from each individual wafer shall be qualified for 1,000 hours minimum, then each screened inspection lot requires 340 hours minimum when selected from qualified wafers.

* 4.4.2.2 Quality levels JAN, JANTX and JANTXV, table E-VIB of MIL-PRF-19500.

	Subgroup	Method	Condition
*	B3	1037	$\Delta T_C = +85^\circ\text{C}$, $I_F = 2$ A minimum.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VII of MIL-PRF-19500. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2, forward voltage test (V_{F1}) and reverse leakage test (I_{R1}) herein. Delta measurements shall be in accordance with table II herein.

	Subgroup	Method	Condition
*	C2	2036	Condition A, weight = 10 lbs (4.5 kg), $t = 15$ seconds. Not applicable for U3 package.
	C5	4081	Limit for thermal resistance for 1N7072CCT3 is 1.6°C/W for each diode. Limit for thermal resistance for 1N7078U3 is 1.6°C/W for each diode.
*	C6	1037	$\Delta T_C = +85^\circ\text{C}$, $I_F = 2$ A minimum.
	C6	1038	Condition A, $V_R = 24$ V dc, $T_J = +100^\circ\text{C}$, $t = 340$ hours minimum (for TX, TXV only); heat sinking allowed. This test shall be extended to 1,000 hours for each wafer. Separate samples may be used.
			As an alternative method a ten dice sample (or 1 die per wafer whichever is greater) from each individual wafer shall be qualified for 1,000 hours minimum, then each screened inspection lot requires 340 hours minimum when selected from qualified wafers.

4.4.4 Group E inspection. Group E inspection shall be conducted in accordance with the tests and conditions specified for subgroup testing in table E-IX of MIL-PRF-19500, and table III herein. Delta measurements shall be in accordance with table II herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

TABLE I. Group A inspection. 1/ 2/

Inspection	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical examination	2071					
<u>Subgroup 2</u>						
Thermal impedance 3/			$Z_{\theta JX}$			°C/W
Forward voltage	4011	Condition B, pulsed test (see 4.5.1)	V_{F1}			
1N7072		$I_F = 7.5 \text{ A (pk)}$			0.48	V dc
1N7078		$I_F = 15 \text{ A (pk)}$			0.51	V dc
Forward voltage	4011	Condition B, pulsed test (see 4.5.1)	V_{F2}			
1N7072		$I_F = 15 \text{ A (pk)}$			0.58	V dc
1N7078		$I_F = 20 \text{ A (pk)}$			0.55	V dc
Forward voltage	4011	Condition B, pulsed test (see 4.5.1)	V_{F3}			
1N7072		$I_F = 16 \text{ A (pk)}$			0.60	V dc
1N7078		$I_F = 30 \text{ A (pk)}$			0.62	V dc
Reverse current	4016	DC method	I_{R1}			
1N7072		$V_R = 30 \text{ V}$			1.0	mA dc
1N7078		$V_R = 30 \text{ V}$			1.0	mA dc
<u>Subgroup 3</u>						
High temperature operation:		$T_C = +125^\circ\text{C}$				
Forward voltage	4011	Condition B, pulsed test (see 4.5.1)	V_{F4}			
1N7072		$I_F = 7.5 \text{ A (pk)}$			0.365	V dc
1N7078		$I_F = 15 \text{ A (pk)}$			0.41	V dc
Forward voltage	4011	Condition B, pulsed test (see 4.5.1)	V_{F5}			
1N7072		$I_F = 15 \text{ A (pk)}$			0.52	V dc
1N7078		$I_F = 20 \text{ A (pk)}$			0.47	V dc
Forward voltage	4011	Condition B, pulsed test (see 4.5.1)	V_{F6}			
1N7072		$I_F = 16 \text{ A (pk)}$			0.54	V dc
1N7078		$I_F = 30 \text{ A (pk)}$			0.57	V dc
Reverse current	4016	DC method;	I_{R2}			
1N7072		$V_R = 30 \text{ V}$			270	mA dc
1N7078		$V_R = 30 \text{ V}$			270	mA dc

See footnotes at end of table.

TABLE I. Group A inspection – Continued. 1/ 2/

Inspection	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
Low temperature operation:		$T_C = -55^\circ\text{C}$				
Forward voltage	4011	Condition B, pulsed test (see 4.5.1)	V_{F7}			
1N7072		$I_F = 7.5 \text{ A (pk)}$			0.57	V dc
1N7078		$I_F = 15 \text{ A (pk)}$			0.58	V dc
Forward voltage	4011	Condition B, pulsed test (see 4.5.1)	V_{F8}			
1N7072		$I_F = 15 \text{ A (pk)}$			0.65	V dc
1N7078		$I_F = 20 \text{ A (pk)}$			0.61	V dc
Forward voltage	4011	Condition B, pulsed test (see 4.5.1)	V_{F9}			
1N7072		$I_F = 16 \text{ A (pk)}$			0.66	V dc
1N7078		$I_F = 30 \text{ A (pk)}$			0.67	V dc
<u>Subgroup 4</u>						
Junction capacitance	4001	$V_R = 5 \text{ V dc}$, $f = 1 \text{ MHz}$, $V_{SIG} = 50 \text{ mV (p-p)}$	C_J			
1N7072					2000	pF
1N7078					2000	pF
<u>Subgroup 5</u>						
Not applicable						
<u>Subgroup 6</u>						
Surge	4066	Condition A, see 1.3, column 4 herein, ten surges each diode. 60 seconds between surges, (see 4.5.1)				
Electrical measurements		See table I, subgroup 2 herein				
<u>Subgroup 7</u>						
Dielectric withstanding voltage	1016	$V_R = 500 \text{ V dc}$; all leads shorted; measure from leads to case	DWV		10	μA
Scope display evaluation	4023	Stable only				
Electrical measurements		See table I, subgroup 2 herein				

1/ For sampling plan, see MIL-PRF-19500.

2/ Each individual diode.

3/ This test required for the following end-point measurements only:

Group B, subgroups 3 and 4 (JANS).

Group B, subgroups 2 and 3 (JAN, JANTX, JANTXV).

Group C, subgroups 2 and 6.

Group E, subgroup 1.

*

TABLE II. Groups B, C, and E delta requirements. 1/ 2/ 3/ 4/ 5/ 6/

Step	Inspection	MIL-STD-750		Symbol	Limits		Unit
		Method	Conditions		Min	Max	
1.	Forward voltage 1N7072 1N7078	4011	Condition B $I_F = 7.5$ A (pk) $I_F = 15$ A (pk) pulsed (see 4.5.1)	ΔV_{F1}	± 50 mV dc from initial reading.		
2.	Forward voltage 1N7072 1N7078	4011	Condition B $I_F = 15$ A (pk) $I_F = 20$ A (pk) pulsed (see 4.5.1)	ΔV_{F2}	± 50 mV dc from initial reading.		
3.	Forward voltage 1N7072 1N7078	4011	Condition B $I_F = 16$ A (pk) $I_F = 30$ A (pk) pulsed (see 4.5.1)	ΔV_{F3}	± 50 mV dc from initial reading.		
4.	Reverse current 1N7072 1N7078	4016	DC Method $V_R = 30$ V $V_R = 30$ V	ΔI_{R1}	± 100 percent from initial reading or ± 500 uA whichever is greater.		
5	Thermal impedance	3101	See 4.3.2	$Z_{\theta JX}$			

1/ Each individual diode.

2/ The delta measurements for table E-VIA (JANS) of MIL-PRF-19500 are as follows:

- Subgroup 3, see table II herein, steps 1, 2, 3, 4, and 5.
- Subgroup 4, see table II herein, steps 1, 2, 3, 4, and 5.
- Subgroup 5, see table II herein, steps 1, 2, 3, and 4.

* 3/ The delta measurements for table E-VIB (JAN, JANTX and JANTXV) of MIL-PRF-19500 are as follows:

- Subgroup 2, see table II herein, steps 1, 2, 3, 4, and 5.
- Subgroup 3, see table II herein, steps 1, 2, 3, 4, and 5.
- Subgroup 6, see table II herein, steps 1, 2, 3, and 4.

4/ The delta measurements for table E-VII of MIL-PRF-19500 are as follows:

- Subgroup 2, see table II herein, steps 1, 2, 3, 4, and 5 for all levels.
- Subgroup 3, see table II herein, steps 1, 2, 3, and 4 for all levels.
- Subgroup 6, see table II herein, steps 1, 2, 3, 4, and 5 for all levels.

5/ The delta measurements for table E-IX of MIL-PRF-19500 are as follows:

- Subgroup 1, see table III herein, steps 1, 2, 3, 4, and 5.
- Subgroup 2, see table III herein, steps 1, 2, 3, and 4.

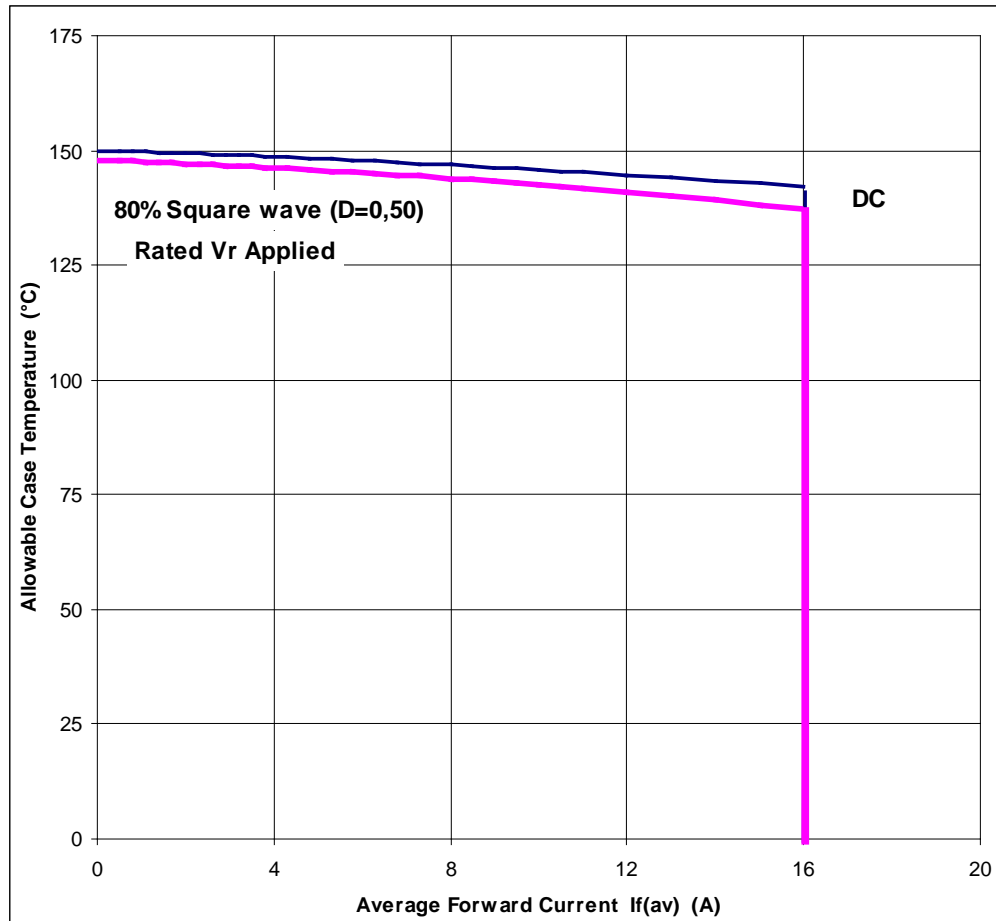
6/ Devices which exceed the table I limits for this test shall not be accepted.

TABLE III. Group E inspection (all quality levels) – for qualification and requalification only.

Inspection	MIL-STD-750		Qualification
	Method	Conditions	
<u>Subgroup 1</u>			45 devices c = 0
Temperature cycling (air to air)	1051	Test condition G, 500 cycles, -55°C to +150°C.	
Hermetic seal	1071		
Electrical measurements		See table I , subgroup 2 and table II herein.	
<u>Subgroup 2</u>			45 devices c = 0
Life test	1048	t = 1,000 hours, T _J = +100°C, V _R = 80 percent rated voltage (see 1.3 , column 2 herein).	
Electrical measurements		See table I subgroup 2 and table II herein.	
<u>Subgroup 4</u>			
Thermal impedance curves		See MIL-PRF-19500 .	
<u>Subgroup 10</u> ^{1/}			
Surge	4066		5 devices c = 0
1N7072		Condition A, T _A = +25°C, I _{FSM} = 150 A, ten surges of 8.3 ms half sine wave. V _R = 0; I _O = 10 A pk.	
1N7078		Condition A, T _A = +25°C, I _{FSM} = 150 A, ten surges of 8.3 ms half sine wave. V _R = 0; I _O = 10 A pk.	
Electrical measurements		See table I subgroup 2 (V _F and I _R only).	

^{1/} Each individual diode.

TEMPERATURE-CURRENT DERATING CURVE **1N7072CCT3**



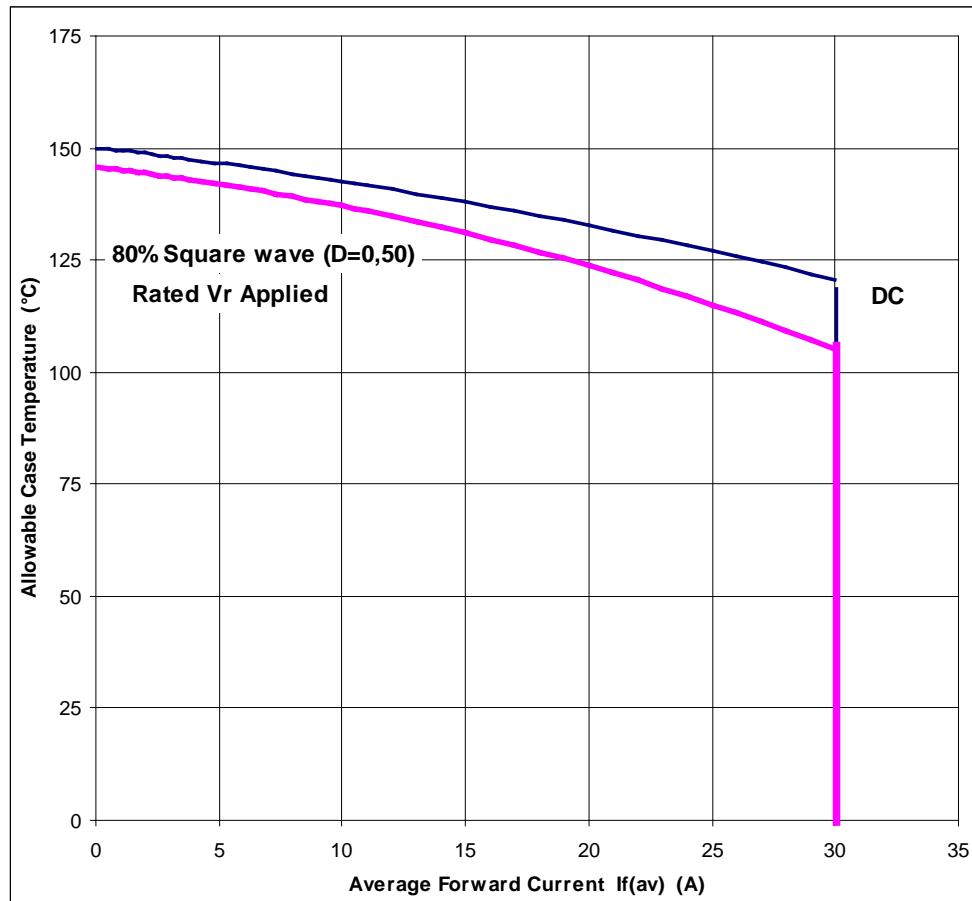
Switch mode operation, 80 percent duty cycle: T_C (°C) (case).
 $R_{\theta JC} = 0.8$ °C/W.

NOTES:

1. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate current for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperature ($T_J \leq 150^\circ\text{C}$) and current rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq 125^\circ\text{C}$, where the maximum temperature of electrical test is performed.
4. Derate design curves chosen at $T_J \leq 125^\circ\text{C}$, and 110°C to show current rating where most users want to limit T_J in their application.

FIGURE 3. Temperature-current derating curve (entire package) for 1N7072CCT3.

TEMPERATURE-CURRENT DERATING CURVE 1N7078U3



Switch mode operation, 80 percent duty cycle: T_C (°C) (case).
 $R_{\theta JC} = 1.6$ °C/W.

NOTES:

1. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate current for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperature ($T_J \leq 150^\circ\text{C}$) and current rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq 125^\circ\text{C}$, where the maximum temperature of electrical test is performed.
4. Derate design curves chosen at $T_J \leq 125^\circ\text{C}$, and 110°C to show current rating where most users want to limit T_J in their application.

FIGURE 4. Temperature-current derating curve (entire package) for 1N7078U3.

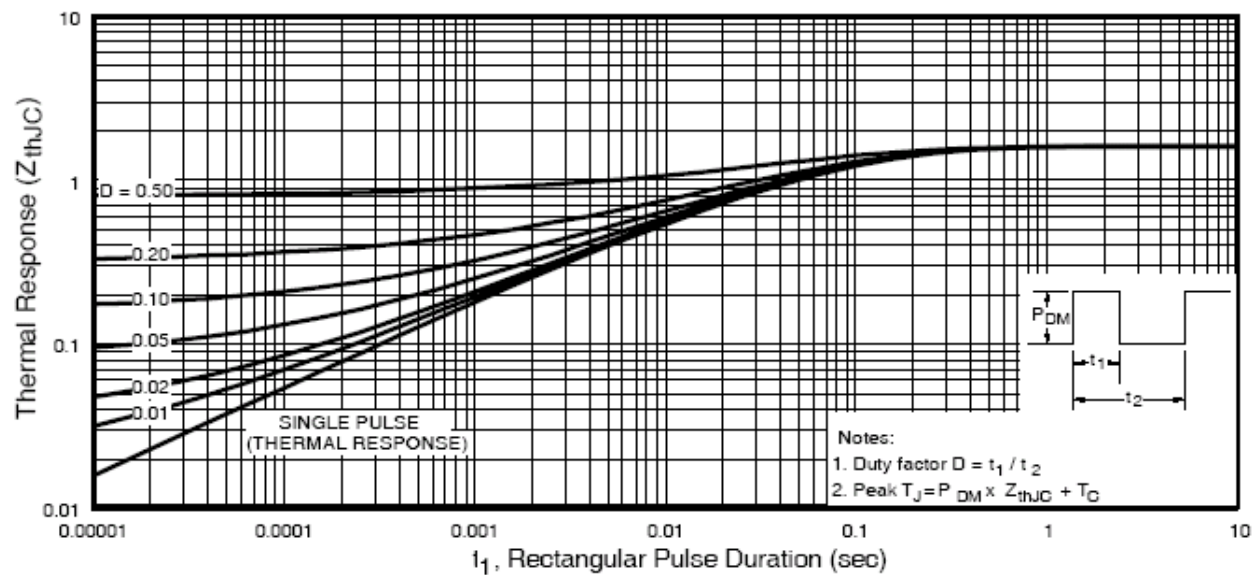


FIGURE 5. Thermal impedance (for each leg) 1N7072CCT3.

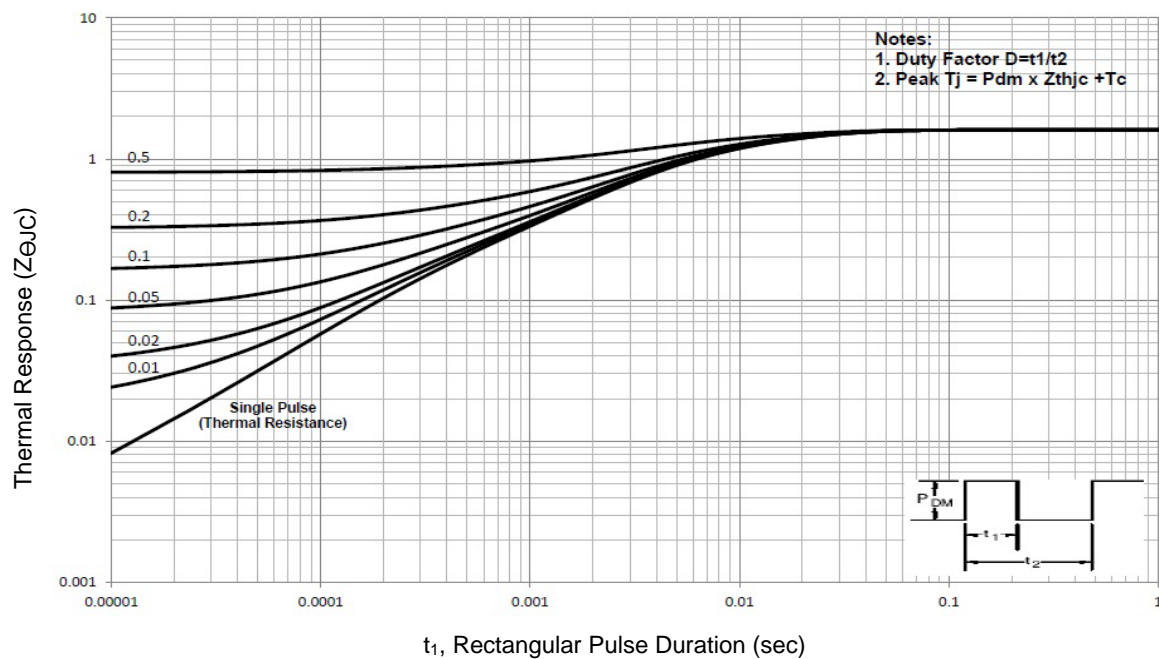
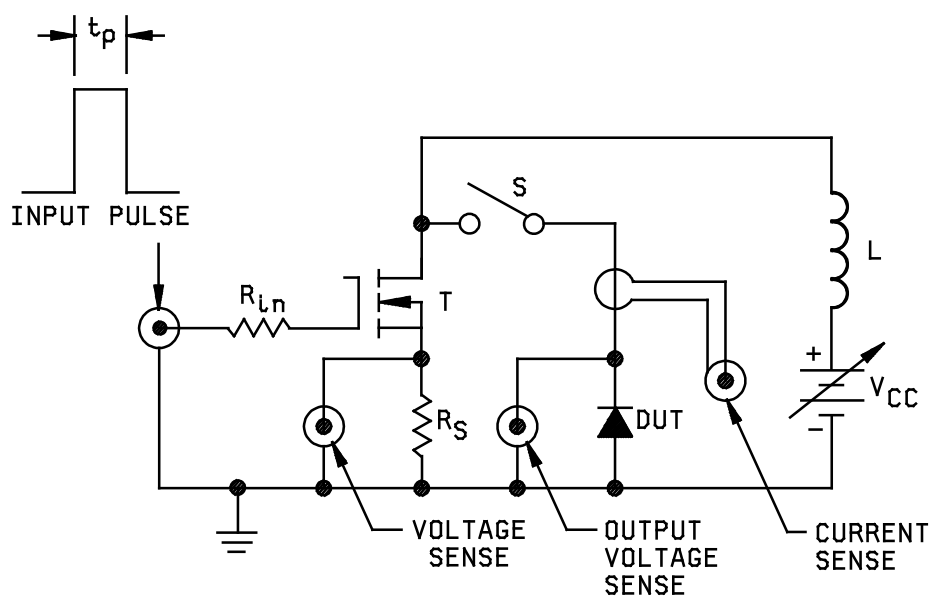


FIGURE 6. Thermal impedance 1N7078U3.



Input pulse $R_{in} = 50$ ohms
 $V_G = 10$ Volts, $R_S = 0.1$ ohms
 $Z_G = 50$ ohms
 $L = 100\mu\text{H}$
 Duty cycle ≤ 1 percent, $T = \text{IRF250/2N6766}$ or equivalent

Procedure:

1. With S open, adjust pulse width to test current of 1 amp through R_S .
2. Close S, verify test current with current sense.
3. Read peak output voltage (see 4.3.3).

FIGURE 7. Avalanche energy test circuit.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory. The notes specified in MIL-PRF-19500 are applicable to this specification.)

6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead material, finish, and formation (see 3.4.2).
- * d. The complete PIN, see 1.5 and 6.6.1.

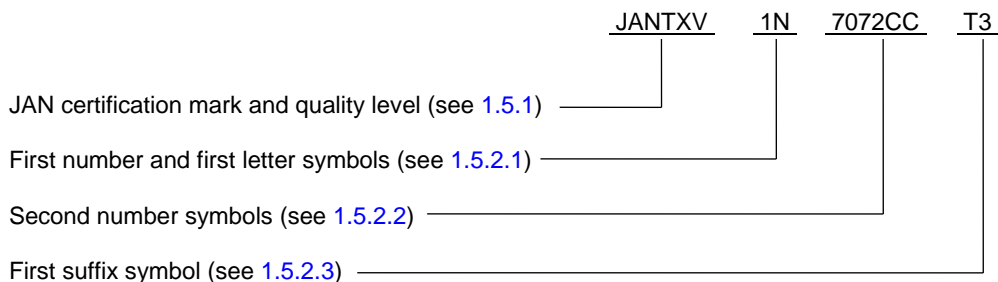
6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML 19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DLA Land and Maritime, ATTN: VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail vqe.chief@dla.mil. An online listing of products qualified to this specification may be found in the Qualified Products Database (QPD) at <https://assist.dla.mil>.

6.4 Cross reference substitution list. A PIN for PIN replacement table follows, and these devices are directly interchangeable.

Non-preferred PIN	Preferred PIN
16SCYQ030C 30SLJQ030	JAN, JANTX, JANTXV, JANS1N7072CCT3 JAN, JANTX, JANTXV, JANS1N7078U3

* 6.5 PIN construction example.

- * 6.5.1 Encapsulated devices The PINs for encapsulated devices are constructed using the following form.



* 6.6 List of PINs.

- * 6.6.1 List of PINs for encapsulated devices. The following is a list of possible PINs for encapsulated devices available on this specification sheet.

PINs for devices of the base quality level	PINs for devices of the "TX" quality level	PINs for devices of the "TXV" quality level	PINs for devices of the "S" quality level
JAN1N7072CCT3	JANTX1N7072CCT3	JANTXV1N7072CCT3	JANS1N7072CCT3
JAN1N7078U3	JANTX1N7078U3	JANTXV1N7078U3	JANS1N7078U3

- * 6.7 Request for new types and configurations. Requests for new device types or configurations for inclusions in this specification sheet should be submitted to: DLA Land and Maritime, ATTN: VAC, Post Office Box 3990, Columbus, OH 43218-3990 or by electronic mail at Semiconductor@dla.mil or by facsimile (614) 693-1642 or DSN 850-6939.
- * 6.8 Changes from previous issue. The margins of this specification are marked with asterisks to indicate where changes from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the last previous issue.

Custodians:
 Army - CR
 Navy - EC
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Review activities
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Preparing activity:
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 (Project 5961-2016-032)

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <https://assist.dla.mil/>.